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Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8347ezujdb

- Address translation units for address mapping between host and peripheral
- Dual address cycle for target
- Internal configuration registers accessible from PCI
- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, IEEE Std. 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs):
 - Public key execution unit (PKEU) :
 - RSA and Diffie-Hellman algorithms
 - Programmable field size up to 2048 bits
 - Elliptic curve cryptography
 - F2m and F(p) modes
 - Programmable field size up to 511 bits
 - Data encryption standard (DES) execution unit (DEU)
 - DES and 3DES algorithms
 - Two key (K1, K2) or three key (K1, K2, K3) for 3DES
 - ECB and CBC modes for both DES and 3DES
 - Advanced encryption standard unit (AESU)
 - Implements the Rijndael symmetric-key cipher
 - Key lengths of 128, 192, and 256 bits
 - ECB, CBC, CCM, and counter (CTR) modes
 - XOR parity generation accelerator for RAID applications
 - ARC four execution unit (AFEU)
 - Stream cipher compatible with the RC4 algorithm
 - 40- to 128-bit programmable key
 - Message digest execution unit (MDEU)
 - SHA with 160-, 224-, or 256-bit message digest
 - MD5 with 128-bit message digest
 - HMAC with either algorithm
 - Random number generator (RNG)
 - Four crypto-channels, each supporting multi-command descriptor chains
 - Static and/or dynamic assignment of crypto-execution units through an integrated controller
 - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- Universal serial bus (USB) dual role controller
 - USB on-the-go mode with both device and host functionality
 - Complies with USB specification Rev. 2.0
 - Can operate as a stand-alone USB device
 - One upstream facing port
 - Six programmable USB endpoints

Table 4. MPC8347EA Power Dissipation¹ (continued)

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at $T_J = 65$	Typical ^{2,3}	Maximum ⁴	Unit
TBGA	333	333	2.0	3.0	3.2	W
		166	1.8	2.8	2.9	W
	400	266	2.1	3.0	3.3	W
		133	1.9	2.9	3.1	W
	450	300	2.3	3.2	3.5	W
		150	2.1	3.0	3.2	W
	500	333	2.4	3.3	3.6	W
		166	2.2	3.1	3.4	W
	533	266	2.4	3.3	3.6	W
		133	2.2	3.1	3.4	W
	667 ^{5,6}	333	3.5	4.6	5	W

¹ The values do not include I/O supply power (OV_{DD} , LV_{DD} , GV_{DD}) or AV_{DD} . For I/O power values, see [Table 5](#).

² Typical power is based on a voltage of $V_{DD} = 1.2$ V, a junction temperature of $T_J = 105^\circ\text{C}$, and a Dhrystone benchmark application.

³ Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.

⁴ Maximum power is based on a voltage of $V_{DD} = 1.2$ V, worst case process, a junction temperature of $T_J = 105^\circ\text{C}$, and an artificial smoke test.

⁵ Typical power is based on a voltage of $V_{DD} = 1.3$ V, a junction temperature of $T_J = 105^\circ\text{C}$, and a Dhrystone benchmark application.

⁶ Maximum power is based on a voltage of $V_{DD} = 1.3$ V, worst case process, a junction temperature of $T_J = 105^\circ\text{C}$, and an artificial smoke test.

Table 11 lists the PLL and DLL lock times.

Table 11. PLL and DLL Lock Times

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	μ s	—
DLL lock times	7680	122,880	csb_clk cycles	1, 2

Notes:

1. DLL lock times are a function of the ratio between the output clock and the coherency system bus clock (csb_clk). A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The csb_clk is determined by the CLKIN and system PLL ratio. See [Section 19, “Clocking.”](#)

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8347EA. Note that DDR SDRAM is $GV_{DD}(typ) = 2.5$ V and DDR2 SDRAM is $GV_{DD}(typ) = 1.8$ V. The AC electrical specifications are the same for DDR and DDR2 SDRAM.

NOTE

The information in this document is accurate for revision 3.0 silicon and later. For information on revision 1.1 silicon and earlier versions see the *MPC8347E PowerQUICC II Pro Integrated Host Processor Hardware Specifications*. See [Section 22.1, “Part Numbers Fully Addressed by This Document,”](#) for silicon revision level determination.

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

Table 12 provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8347EA when $GV_{DD}(typ) = 1.8$ V.

Table 12. DDR2 SDRAM DC Electrical Characteristics for $GV_{DD}(typ) = 1.8$ V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	-9.9	9.9	μ A	4
Output high current ($V_{OUT} = 1.420$ V)	I_{OH}	-13.4	—	mA	—

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) \pm 5%.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/ $\overline{MCK[n]}$ crossing) (PBGA package)	t_{MCK}	5	—	ns	2
MCK[n] cycle time, (MCK[n]/ $\overline{MCK[n]}$ crossing) (TBGA package)	t_{MCK}	7.5	—	ns	2
ADDR/CMD/MODT output setup with respect to MCK 400 MHz 333 MHz 266 MHz 200 MHz	t_{DDKHAS}	1.95 2.40 3.15 4.20	— — — —	ns	3
ADDR/CMD/MODT output hold with respect to MCK 400 MHz 333 MHz 266 MHz 200 MHz	t_{DDKHAX}	1.95 2.40 3.15 4.20	— — — —	ns	3
$\overline{MCS}(n)$ output setup with respect to MCK 400 MHz 333 MHz 266 MHz 200 MHz	t_{DDKHCS}	1.95 2.40 3.15 4.20	— — — —	ns	3
$\overline{MCS}(n)$ output hold with respect to MCK 400 MHz 333 MHz 266 MHz 200 MHz	t_{DDKHGX}	1.95 2.40 3.15 4.20	— — — —	ns	3
MCK to MDQS Skew	t_{DDKMHM}	−0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS 400 MHz 333 MHz 266 MHz 200 MHz	t_{DDKHDS} , t_{DDKLDS}	700 775 1100 1200	— — — —	ps	5
MDQ/MECC/MDM output hold with respect to MDQS 400 MHz 333 MHz	t_{DDKHDX} , t_{DDKLDX}	700 900	— —	ps	5

8.1.1 TSEC DC Electrical Characteristics

GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in [Table 23](#) and [Table 24](#). The RGMII and RTBI signals in [Table 24](#) are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 23. GMII/TBI and MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD}^2	—		2.97	3.63	V
Output high voltage	V_{OH}	$I_{OH} = -4.0 \text{ mA}$	$LV_{DD} = \text{Min}$	2.40	$LV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 4.0 \text{ mA}$	$LV_{DD} = \text{Min}$	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	$LV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	—	-0.3	0.90	V
Input high current	I_{IH}	$V_{IN}^1 = LV_{DD}$		—	40	μA
Input low current	I_{IL}	$V_{IN}^1 = \text{GND}$		-600	—	μA

Notes:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).
2. GMII/MII pins not needed for RGMII or RTBI operation are powered by the OV_{DD} supply.

Table 24. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$	$LV_{DD} = \text{Min}$	2.00	$LV_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0 \text{ mA}$	$LV_{DD} = \text{Min}$	$\text{GND} - 0.3$	0.40	V
Input high voltage	V_{IH}	—	$LV_{DD} = \text{Min}$	1.7	$LV_{DD} + 0.3$	V
Input low voltage	V_{IL}	—	$LV_{DD} = \text{Min}$	-0.3	0.70	V
Input high current	I_{IH}	$V_{IN}^1 = LV_{DD}$		—	10	μA
Input low current	I_{IL}	$V_{IN}^1 = \text{GND}$		-15	—	μA

Note:

1. The symbol V_{IN} , in this case, represents the LV_{IN} symbol referenced in [Table 1](#) and [Table 2](#).

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

Table 27. MII Transmit AC Timing Specifications (continued)

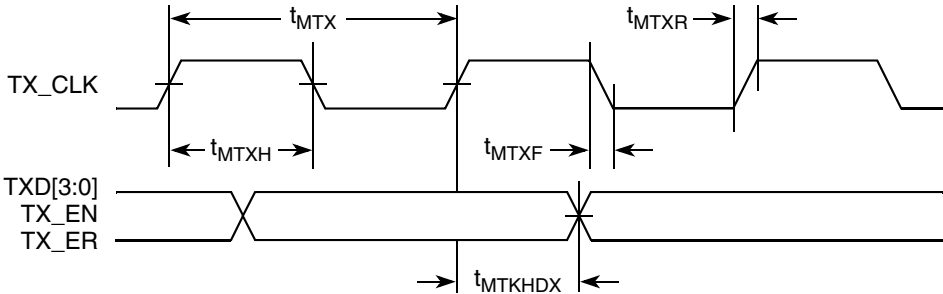
At recommended operating conditions with V_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
TX_CLK data clock rise (20%–80%)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}	1.0	—	4.0	ns

Note:

- The symbols for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 11 shows the MII transmit AC timing diagram.


Figure 11. MII Transmit AC Timing Diagram

8.2.2.2 MII Receive AC Timing Specifications

Table 28 provides the MII receive AC timing specifications.

Table 28. MII Receive AC Timing Specifications

At recommended operating conditions with V_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
RX_CLK clock period 10 Mbps	t_{MRX}	—	400	—	ns
RX_CLK clock period 100 Mbps	t_{MRX}	—	40	—	ns
RX_CLK duty cycle	t_{MRXH}/t_{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns

8.2.3.1 TBI Transmit AC Timing Specifications

Table 29 provides the TBI transmit AC timing specifications.

Table 29. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
GTX_CLK clock period	t_{TTX}	—	8.0	—	ns
GTX_CLK duty cycle	t_{TTXH}/t_{TTX}	40	—	60	%
GTX_CLK to TBI data TXD[7:0], TX_ER, TX_EN delay	t_{TTKHDX}	1.0	—	5.0	ns
GTX_CLK clock rise (20%–80%)	t_{TTXR}	—	—	1.0	ns
GTX_CLK clock fall time (80%–20%)	t_{TTXF}	—	—	1.0	ns

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$ for inputs and $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$ for outputs. For example, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 14 shows the TBI transmit AC timing diagram.

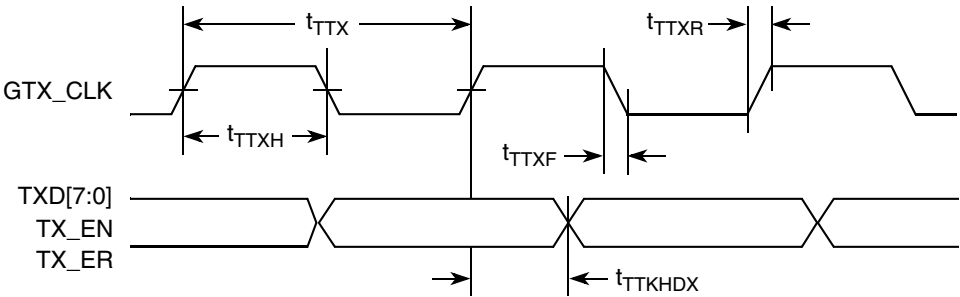


Figure 14. TBI Transmit AC Timing Diagram

8.2.3.2 TBI Receive AC Timing Specifications

Table 30 provides the TBI receive AC timing specifications.

Table 30. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of $3.3\text{ V} \pm 10\%$.

Parameter/Condition	Symbol ¹	Min	Typ	Max	Unit
PMA_RX_CLK clock period	t_{TRX}		16.0		ns
PMA_RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%

Figure 16 shows the RBMII and RTBI AC timing and multiplexing diagrams.

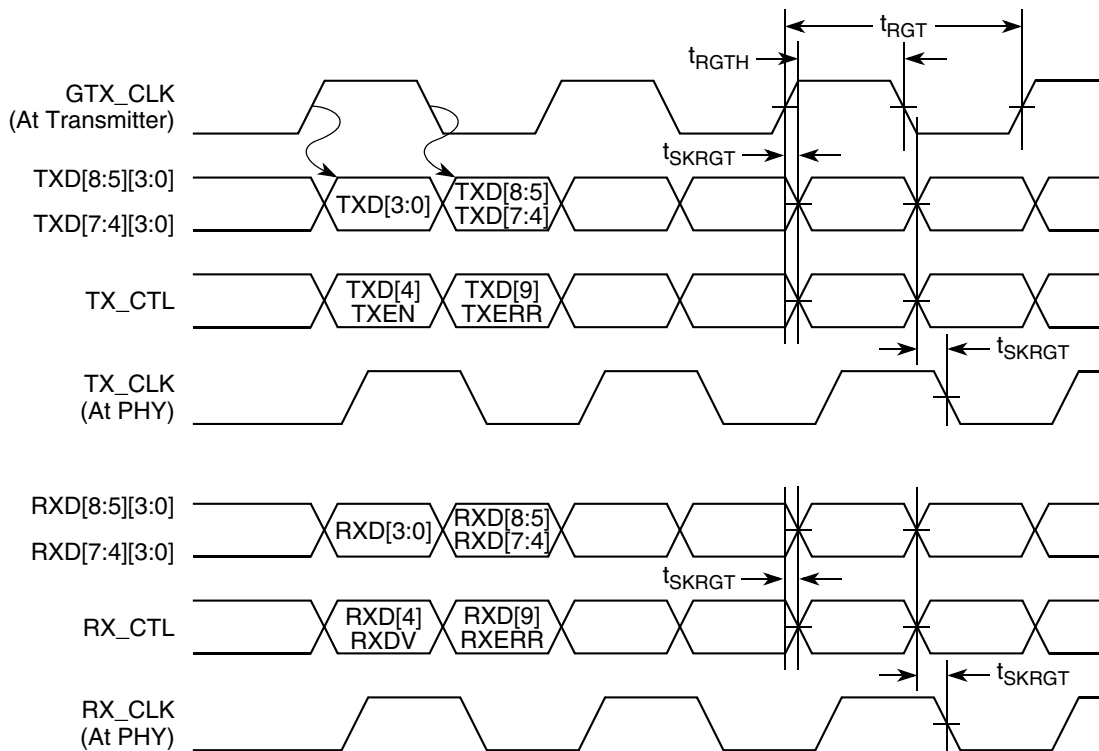


Figure 16. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to the MII management interface signals management data input/output (MDIO) and management data clock (MDC). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in [Section 8.1, “Three-Speed Ethernet Controller \(TSEC\)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics.”](#)

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 2.5 or 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in [Table 32](#) and [Table 33](#).

Table 32. MII Management DC Electrical Characteristics Powered at 2.5 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (2.5 V)	V_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	$I_{OH} = -1.0 \text{ mA}$	$V_{DD} = \text{Min}$	2.00	$V_{DD} + 0.3$	V
Output low voltage	V_{OL}	$I_{OL} = 1.0 \text{ mA}$	$V_{DD} = \text{Min}$	$\text{GND} - 0.3$	0.40	V
Input high voltage	V_{IH}	—	$V_{DD} = \text{Min}$	1.7	—	V
Input low voltage	V_{IL}	—	$V_{DD} = \text{Min}$	-0.3	0.70	V

Table 41. JTAG AC Timing Specifications (Independent of CLKIN)¹ (continued)

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock to output high impedance: Boundary-scan data TDO	t_{JTKLDZ} t_{JTKLOZ}	2 2	19 9	ns	5, 6

Notes:

1. All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50 Ω load (see Figure 18). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.
2. The symbols for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{JTDVXH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDVXH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
3. \overline{TRST} is an asynchronous level sensitive signal. The setup time is for test purposes only.
4. Non-JTAG signal input timing with respect to t_{TCLK} .
5. Non-JTAG signal output timing with respect to t_{TCLK} .
6. Guaranteed by design and characterization.

Figure 27 provides the AC test load for TDO and the boundary-scan outputs of the MPC8347EA.

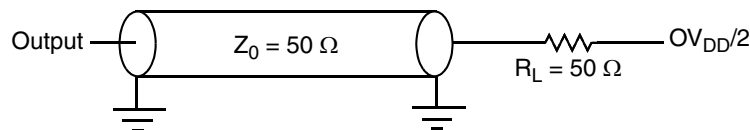

Figure 27. AC Test Load for the JTAG Interface

Figure 28 provides the JTAG clock input timing diagram.

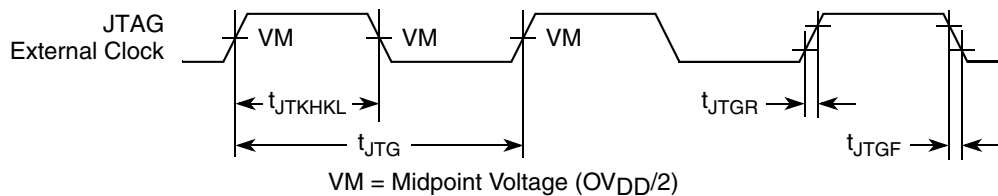

Figure 28. JTAG Clock Input Timing Diagram

Figure 29 provides the \overline{TRST} timing diagram.

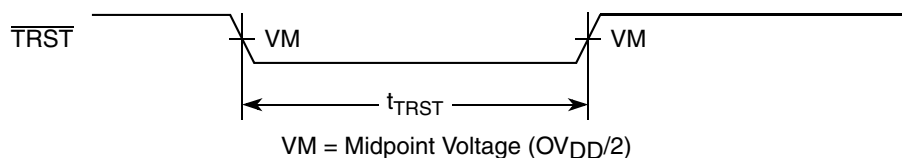

Figure 29. \overline{TRST} Timing Diagram

Figure 30 provides the boundary-scan timing diagram.

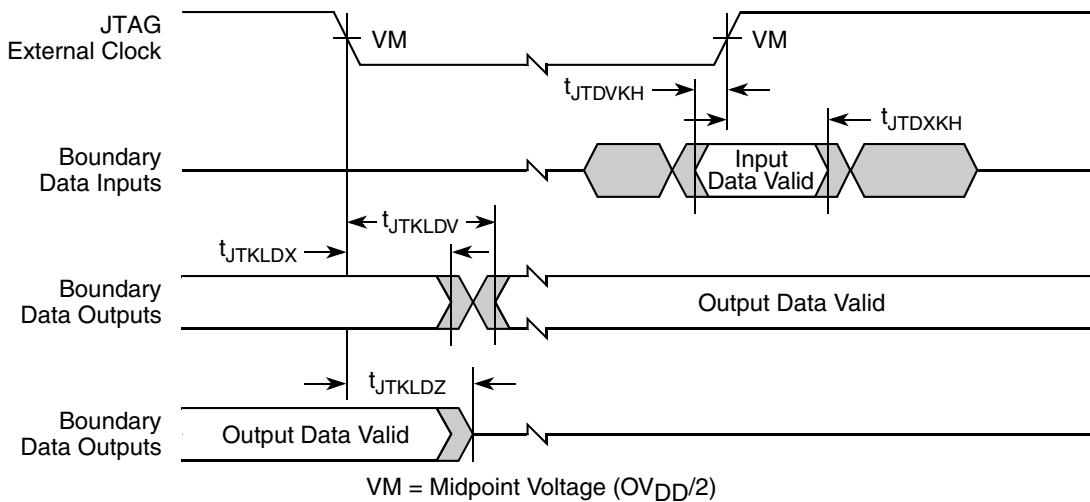


Figure 30. Boundary-Scan Timing Diagram

Figure 31 provides the test access port timing diagram.

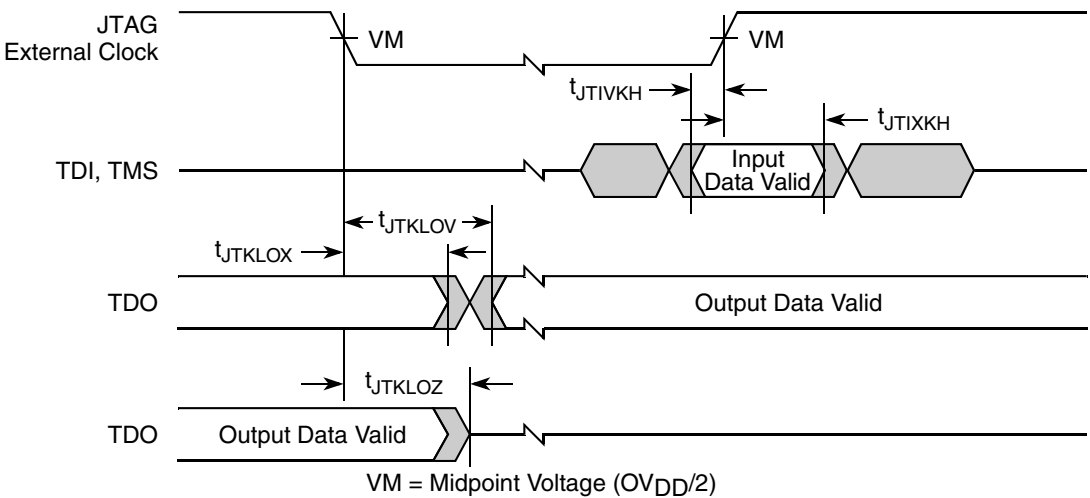


Figure 31. Test Access Port Timing Diagram

Table 43. I²C AC Electrical Specifications (continued)

Parameter	Symbol ¹	Min	Max	Unit
Fall time of both SDA and SCL signals ⁵	t_{I2CF}	—	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μ s
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μ s
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V

Notes:

1. The symbols for timing specifications follow the pattern of $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$ for inputs and $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) goes invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaches the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The device provides a hold time of at least 300 ns for the SDA signal (referred to the $V_{IH(min)}$ of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} must be met only if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.
- 5.)The device does not follow the "I²C-BUS Specifications" version 2.1 regarding the t_{I2CF} AC parameter.

Figure 32 provides the AC test load for the I²C.

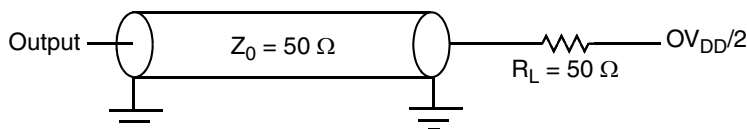

Figure 32. I²C AC Test Load

Figure 33 shows the AC timing diagram for the I²C bus.

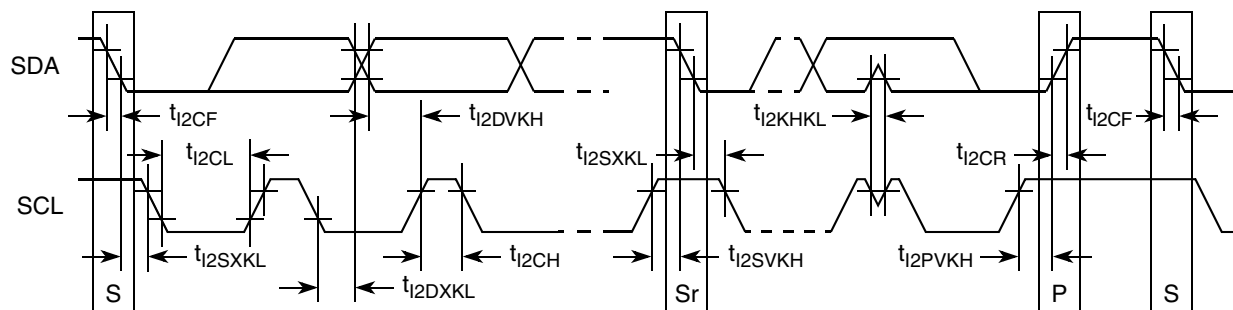

Figure 33. I²C Bus AC Timing Diagram

Figure 38 and Figure 39 represent the AC timings from Table 54. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 38 shows the SPI timings in slave mode (external clock).

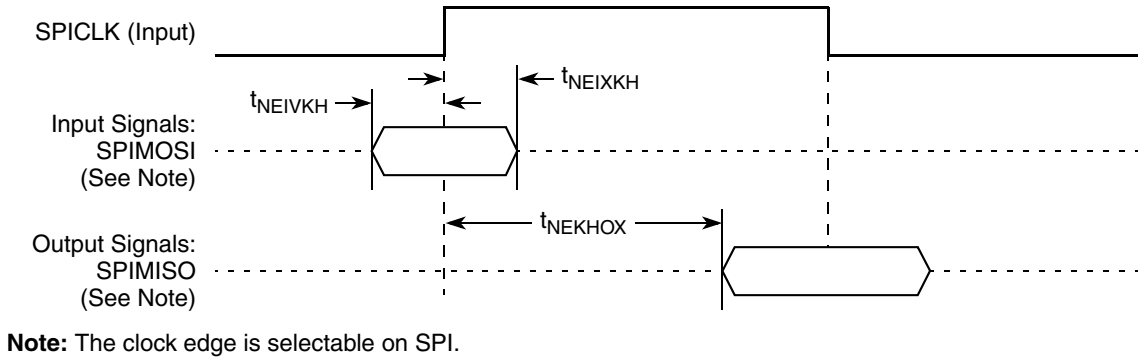


Figure 38. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 39 shows the SPI timings in master mode (internal clock).

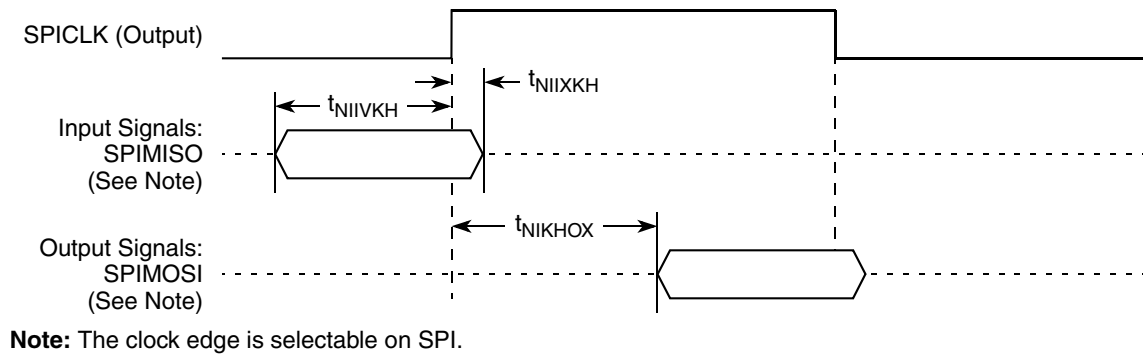


Figure 39. SPI AC Timing in Master Mode (Internal Clock) Diagram

18 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8347EA is available in two packages—a tape ball grid array (TBGA) and a plastic ball grid array (PBGA). See Section 18.1, “Package Parameters for the MPC8347EA TBGA,” Section 18.2, “Mechanical Dimensions for the MPC8347EA TBGA,” Section 18.3, “Package Parameters for the MPC8347EA PBGA,” and Section 18.4, “Mechanical Dimensions for the MPC8347EA PBGA.”

18.1 Package Parameters for the MPC8347EA TBGA

The package parameters are provided in the following list. The package type is 35 mm × 35 mm, 672 tape ball grid array (TBGA).

Package outline	35 mm × 35 mm
Interconnects	672

Table 55. MPC8347EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LALÉ	AK24	O	OV _{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AP27	I/O	OV _{DD}	—
LGPL1/LSDWE/cfg_reset_source1	AL25	I/O	OV _{DD}	—
LGPL2/LSDRAS/LOE	AJ24	O	OV _{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	AN27	I/O	OV _{DD}	—
LGPL4/LGTÁ/LUPWAIT/LPBSE	AP28	I/O	OV _{DD}	13
LGPL5/cfg_clkin_div	AL26	I/O	OV _{DD}	—
LCKE	AM27	O	OV _{DD}	—
LCLK[0:2]	AN28, AK26, AP29	O	OV _{DD}	—
LSYNC_OUT	AM12	O	OV _{DD}	—
LSYNC_IN	AJ10	I	OV _{DD}	—
General Purpose I/O Timers				
GPIO1[0]/DMA_DREQ0/GTM1_TIN1/ GTM2_TIN2	F24	I/O	OV _{DD}	—
GPIO1[1]/DMA_DACK0/GTM1_TGATE1/ GTM2_TGATE2	E24	I/O	OV _{DD}	—
GPIO1[2]/DMA_DDONE0/GTM1_TOUT1	B25	I/O	OV _{DD}	—
GPIO1[3]/DMA_DREQ1/GTM1_TIN2/ GTM2_TIN1	D24	I/O	OV _{DD}	—
GPIO1[4]/DMA_DACK1/GTM1_TGATE2/ GTM2_TGATE1	A25	I/O	OV _{DD}	—
GPIO1[5]/DMA_DDONE1/GTM1_TOUT2/ GTM2_TOUT1	B24	I/O	OV _{DD}	—
GPIO1[6]/DMA_DREQ2/GTM1_TIN3/ GTM2_TIN4	A24	I/O	OV _{DD}	—
GPIO1[7]/DMA_DACK2/GTM1_TGATE3/ GTM2_TGATE4	D23	I/O	OV _{DD}	—
GPIO1[8]/DMA_DDONE2/GTM1_TOUT3	B23	I/O	OV _{DD}	—
GPIO1[9]/DMA_DREQ3/GTM1_TIN4/ GTM2_TIN3	A23	I/O	OV _{DD}	—
GPIO1[10]/DMA_DACK3/GTM1_TGATE4/ GTM2_TGATE3	F22	I/O	OV _{DD}	—
GPIO1[11]/DMA_DDONE3/GTM1_TOUT4/ GTM2_TOUT3	E22	I/O	OV _{DD}	—
USB Port 1				
MPH1_D0_ENABLEN/DR_D0_ENABLEN	A26	I/O	OV _{DD}	—
MPH1_D1_SER_TXD/DR_D1_SER_TXD	B26	I/O	OV _{DD}	—
MPH1_D2_VMO_SE0/DR_D2_VMO_SE0	D25	I/O	OV _{DD}	—

Table 55. MPC8347EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Test				
TEST	D22	I	OV _{DD}	6
TEST_SEL	AL13	I	OV _{DD}	7
PMC				
<u>QUIESCE</u>	A18	O	OV _{DD}	—
System Control				
<u>PORESET</u>	C18	I	OV _{DD}	—
<u>HRESET</u>	B18	I/O	OV _{DD}	1
<u>SRESET</u>	D18	I/O	OV _{DD}	2
Thermal Management				
THERM0	K32	I	—	9
Power and Ground Signals				
AV _{DD1}	L31	Power for e300 PLL (1.2 V) nominal, 1.3 V for 667 MHz)	AV _{DD1}	—
AV _{DD2}	AP12	Power for system PLL (1.2 V) nominal, 1.3 V for 667 MHz)	AV _{DD2}	—
AV _{DD3}	AE1	Power for DDR DLL (1.2 V) nominal, 1.3 V for 667 MHz)	—	—
AV _{DD4}	AJ13	Power for LBIU DLL (1.2 V) nominal, 1.3 V for 667 MHz)	AV _{DD4}	—
GND	A1, A34, C1, C7, C10, C11, C15, C23, C25, C28, D1, D8, D20, D30, E7, E13, E15, E17, E18, E21, E23, E25, E32, F6, F19, F27, F30, F34, G31, H5, J4, J34, K30, L5, M2, M5, M30, M33, N3, N5, P30, R5, R32, T5, T30, U6, U29, U33, V2, V5, V30, W6, W30, Y30, AA2, AA30, AB2, AB6, AB30, AC3, AC6, AD31, AE5, AF2, AF5, AF31, AG30, AG31, AH4, AJ3, AJ19, AJ22, AK7, AK13, AK14, AK16, AK18, AK20, AK25, AK28, AL3, AL5, AL10, AL12, AL22, AL27, AM1, AM6, AM7, AN12, AN17, AN34, AP1, AP8, AP34	—	—	—

Table 56. MPC8347EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_TRDY	A13	I/O	OV _{DD}	5
PCI1_IRDY	E13	I/O	OV _{DD}	5
PCI1_STOP	C13	I/O	OV _{DD}	5
PCI1_DEVSEL	B13	I/O	OV _{DD}	5
PCI1_IDSEL	C17	I	OV _{DD}	—
PCI1_SERR	C12	I/O	OV _{DD}	5
PCI1_PERR	B12	I/O	OV _{DD}	5
PCI1_REQ[0]	A21	I/O	OV _{DD}	
PCI1_REQ[1]/CPCI1_HS_ES	C19	I	OV _{DD}	—
PCI1_REQ[2:4]	C18, A19, E20	I	OV _{DD}	—
PCI1_GNT0	B20	I/O	OV _{DD}	—
PCI1_GNT1/CPCI1_HS_LED	C20	O	OV _{DD}	—
PCI1_GNT2/CPCI1_HS_ENUM	B19	O	OV _{DD}	—
PCI1_GNT[3:4]	A20, E18	O	OV _{DD}	—
M66EN	L26	I	OV _{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	AC25, AD27, AD25, AH27, AE28, AD26, AD24, AF27, AF25, AF28, AH24, AG26, AE25, AG25, AH26, AH25, AG22, AH22, AE21, AD19, AE22, AF23, AE19, AG20, AG19, AD17, AE16, AF16, AF18, AG18, AH17, AH16, AG9, AD12, AG7, AE8, AD11, AH9, AH8, AF6, AF8, AE6, AF1, AE4, AG8, AH3, AG3, AG4, AH2, AD7, AB4, AB3, AG1, AD5, AC2, AC1, AC4, AA3, Y4, AA4, AB1, AB2, Y5, Y3	I/O	GV _{DD}	—
MECC[0:4]/MSRCID[0:4]	AG13, AE14, AH12, AH10, AE15	I/O	GV _{DD}	—
MECC[5]/MDVAL	AH14	I/O	GV _{DD}	—
MECC[6:7]	AE13, AH11	I/O	GV _{DD}	—
MDM[0:8]	AG28, AG24, AF20, AG17, AE9, AH5, AD1, AA2, AG12	O	GV _{DD}	—
MDQS[0:8]	AE27, AE26, AE20, AH18, AG10, AF5, AC3, AA1, AH13	I/O	GV _{DD}	—
MBA[0:1]	AF10, AF11	O	GV _{DD}	—
MA[0:14]	AF13, AF15, AG16, AD16, AF17, AH20, AH19, AH21, AD18, AG21, AD13, AF21, AF22, AE1, AA5	O	GV _{DD}	—
MWE	AD10	O	GV _{DD}	—

Table 56. MPC8347EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MRAS	AF7	O	GV _{DD}	—
MCAS	AG6	O	GV _{DD}	—
$\overline{\text{MCS}}[0:3]$	AE7, AH7, AH4, AF2	O	GV _{DD}	—
MCKE[0:1]	AG23, AH23	O	GV _{DD}	3
MCK[0:5]	AH15, AE24, AE2, AF14, AE23, AD3	O	GV _{DD}	—
$\overline{\text{MCK}}[0:5]$	AG15, AD23, AE3, AG14, AF24, AD2	O	GV _{DD}	—
MODT[0:3]	AG5, AD4, AH6, AF4	O	GV _{DD}	—
MBA[2]	AD22	O	GV _{DD}	—
MDIC0	AG11	I/O	—	9
MDIC1	AF12	I/O	—	9
Local Bus Controller Interface				
LAD[0:31]	T4, T5, T1, R2, R3, T2, R1, R4, P1, P2, P3, P4, N1, N4, N2, N3, M1, M2, M3, N5, M4, L1, L2, L3, K1, M5, K2, K3, J1, J2, L5, J3	I/O	OV _{DD}	—
LDP[0]/ $\overline{\text{CKSTOP_OUT}}$	H1	I/O	OV _{DD}	—
LDP[1]/ $\overline{\text{CKSTOP_IN}}$	K5	I/O	OV _{DD}	—
LDP[2]/ $\overline{\text{LCS}}[4]$	H2	I/O	OV _{DD}	—
LDP[3]/ $\overline{\text{LCS}}[5]$	G1	I/O	OV _{DD}	—
LA[27:31]	J4, H3, G2, F1, G3	O	OV _{DD}	—
$\overline{\text{LCS}}[0:3]$	J5, H4, F2, E1	O	OV _{DD}	—
$\overline{\text{LWE}}[0:3]/\text{LSDDQM}[0:3]/\overline{\text{LBS}}[0:3]$	F3, G4, D1, E2	O	OV _{DD}	—
LBCTL	H5	O	OV _{DD}	—
LALE	E3	O	OV _{DD}	—
LGPL0/LSDA10/cfg_reset_source0	F4	I/O	OV _{DD}	—
LGPL1/ $\overline{\text{LSDWE}}$ /cfg_reset_source1	D2	I/O	OV _{DD}	—
LGPL2/ $\overline{\text{LSDRAS}}$ /LOE	C1	O	OV _{DD}	—
LGPL3/ $\overline{\text{LSDCAS}}$ /cfg_reset_source2	C2	I/O	OV _{DD}	—
LGPL4/ $\overline{\text{LGTA}}$ /LUPWAIT/LPBSE	C3	I/O	OV _{DD}	12
LGPL5/cfg_clkin_div	B3	I/O	OV _{DD}	—
LCKE	E4	O	OV _{DD}	—
LCLK[0:2]	D4, A3, C4	O	OV _{DD}	—
LSYNC_OUT	U3	O	OV _{DD}	—
LSYNC_IN	Y2	I	OV _{DD}	—

19 Clocking

Figure 42 shows the internal distribution of the clocks.

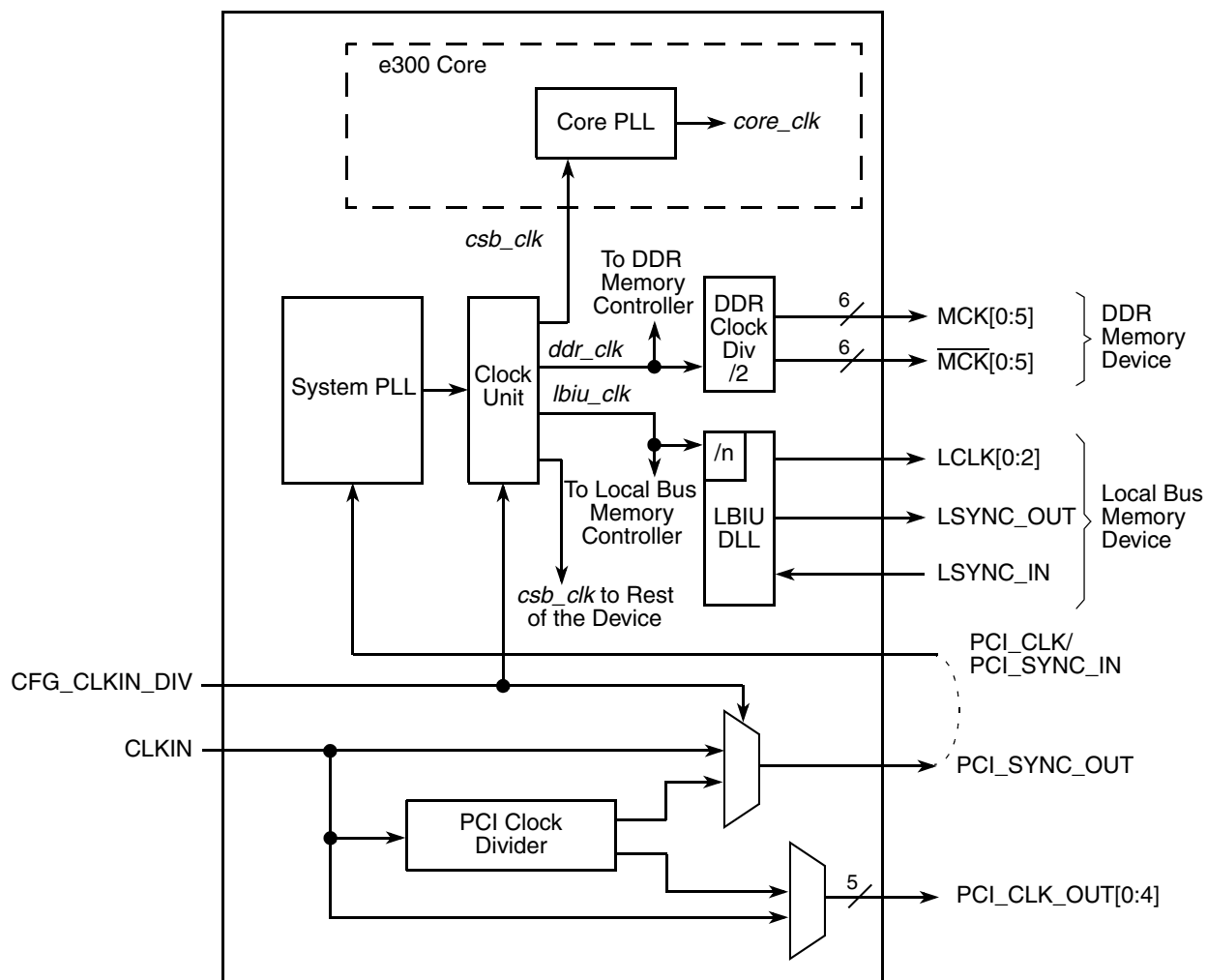


Figure 42. MPC8347EA Clock Subsystem

The primary clock source can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. When the MPC8347EA is configured as a PCI host device, CLKIN is its primary input clock. CLKIN feeds the PCI clock divider ($\div 2$) and the multiplexers for PCI_SYNC_OUT and PCI_CLK_OUT. The CFG_CLKIN_DIV configuration input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCICD n] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUT n signals.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subsystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the MPC8347EA to function. When the device is configured as a PCI agent device, PCI_CLK is the primary input clock and the CLKIN signal should be tied to GND.

Table 67 and Table 68 show heat sink thermal resistance for TBGA and PBGA of the MPC8347EA.

Table 67. Heat Sink and Thermal Resistance of MPC8347EA (TBGA)

Heat Sink Assuming Thermal Grease	Air Flow	35 × 35 mm TBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	10
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	6.5
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	5.6
AAVID 31 × 35 × 23 mm pin fin	Natural convection	8.4
AAVID 31 × 35 × 23 mm pin fin	1 m/s	4.7
AAVID 31 × 35 × 23 mm pin fin	2 m/s	4
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	5.7
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	3.5
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	2.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	6.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	4.1
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	2.8
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	3.1

Table 68. Heat Sink and Thermal Resistance of MPC8347EA (PBGA)

Heat Sink Assuming Thermal Grease	Air Flow	29 × 29 mm PBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	13.5
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	9.6
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	8.8
AAVID 31 × 35 × 23 mm pin fin	Natural convection	11.3
AAVID 31 × 35 × 23 mm pin fin	1 m/s	8.1
AAVID 31 × 35 × 23 mm pin fin	2 m/s	7.5
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	9.1
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	7.1
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	6.5
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	10.1
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	7.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	6.6
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	6.9

Shin-Etsu MicroSi, Inc.
10028 S. 51st St.
Phoenix, AZ 85044
Internet: www.microsi.com

888-642-7674

The Bergquist Company
18930 West 78th St.
Chanhassen, MN 55317
Internet: www.bergquistcompany.com

800-347-4572

20.3 Heat Sink Attachment

When heat sinks are attached, an interface material is required, preferably thermal grease and a spring clip. The spring clip should connect to the printed-circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces that can lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. The recommended maximum force on the top of the package is 10 lb force (4.5 kg force). Any adhesive attachment should attach to painted or plastic surfaces, and its performance should be verified under the application requirements.

20.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When a heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimize the size of the clearance to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_J = junction temperature (°C)

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

P_D = power dissipation (W)

Table 72. Document Revision History (continued)

Rev. Number	Date	Substantive Change(s)
8	2/2009	<ul style="list-style-type: none"> Added footnote 6 to Table 7. In Section 9.2, "USB AC Electrical Specifications," clarified that AC table is for ULPI only. In Table 39, corrected t_{LBKHOV} parameter to t_{LBKLOV} (output data is driven on falling edge of clock in DLL bypass mode). Similarly, made the same correction to Figure 22, Figure 24, and Figure 25 for output signals. Added footnote 10 and 11 to Table 55 and Table 56. In Section 21.1, "System Clocking," removed "(AVDD1)" and "(AVDD2)" from bulleted list. In Section 21.2, "PLL Power Supply Filtering," in the second paragraph, changed "provide five independent filter circuits," and "the five AVDD pins" to provide four independent filter circuits," and "the four AVDD pins." In Table 58, corrected the max csb_clk to 266 MHz. In Table 64, added PLL configurations 903, 923, A03, A23, and 503 for 533 MHz Added footnote 4 to Table 70. In Table 70, updated note 1 to say the following: "For temperature range = C, processor frequency is limited to 533 (TBGA) and 400 (PBGA) with a platform frequency of 266."
7	4/2007	<ul style="list-style-type: none"> In Table 3, "Output Drive Capability," changed the values in the Output Impedance column and added USB to the seventh row. In Table 4, "Operating Frequencies for TBGA," added column for 400 MHz. In Section 21.7, "Pull-Up Resistor Requirements," deleted last two paragraphs and after first paragraph, added a new paragraph. Deleted Section 21.8, "JTAG Configuration Signals," and Figure 43, "JTAG Interface Connection."
6	3/2007	<ul style="list-style-type: none"> Page 1, updated first paragraph to reflect PowerQUICC II Pro information. In Table 18, "DDR and DDR2 SDRAM Input AC Timing Specifications," added note 2 to t_{CISKEW} and deleted original note 3; renumbered the remaining notes. In Figure 43, "JTAG Interface Connection," updated with new figure. In Table 57, "Operating Frequencies for TBGA," in the 'Coherent system bus frequency (<i>csb_clk</i>)' row, changed the value in the 533 MHz column to 100-333. In Table 63, "Suggested PLL Configurations," under the subhead, '33 MHz CLKIN/PCI_CLK Options,' added row A03 between Ref. No. 724 and 804. Under the subhead '66 MHz CLKIN/PCI_CLK Options,' added row 503 between Ref. No. 305 and 404. For Ref. No. 306, changed the CORE PLL value to 0000110. In Section 23, "Ordering Information," replaced first paragraph and added a note. In Section 23.1, "Part Numbers Fully Addressed by this Document," replaced first paragraph.
5	1/2007	<ul style="list-style-type: none"> In Table 1, "Absolute Maximum Ratings," added (1.36 max for 667-MHz core frequency). In Table 2, "Recommended Operating Conditions," added a row showing nominal core supply voltage of 1.3 V for 667-MHz parts. In Table 4, "MPC8347EA Power Dissipation," added two footnotes to 667-MHz row showing nominal core supply voltage of 1.3 V for 667-MHz parts. In Table 54, "MPC8347EA (TBGA) Pinout Listing," updated V_{DD} row to show nominal core supply voltage of 1.3 V for 667-MHz parts.
4	12/2006	<p>Table 19, "DDR and DDR2 SDRAM Output AC Timing Specifications," modified T_{ddkhd} for 333 MHz from 900 ps to 775 ps.</p>
3	11/2006	<ul style="list-style-type: none"> Updated note in introduction. In the features list in Section 1, "Overview," updated DDR data rate to show 266 MHz for PBGA parts for all silicon revisions, and 400 MHz for DDR2 for TBGA parts for silicon Rev. 2 and 3. In Table 5, "MPC8347EA Typical I/O Power Dissipation," added GV_{DD} 1.8-V values for DDR2; added table footnote to designate rates that apply only to the TBGA package. In Section 23, "Ordering Information," replicated note from document introduction.